

### **Amendments to the Specification:**

Kindly replace the paragraph on page 2, lines 2-5, with the following amended paragraph:

In light of the above, there has been a proposal of adding a sintering auxiliary agent for increasing the sintering density. For example, the publication of Japanese Patent Laid Open Publication No. 2000-247739 describes an attempt of increasing the relative density to 85% to 90% by adding 0.001mol% to 0.5mol% of Bi<sub>2</sub>O<sub>3</sub>.

Kindly replace the paragraph on page 2, lines 20-30, with the following amended paragraph:

The present invention provides : ~~1. A~~ a SrRuO<sub>3</sub> conductive oxide sintered body characterized in that the relative density is 93% or more; ~~2. A conductive oxide sintered body according to paragraph 1 above, characterized in that the resistivity is 500μΩcm or less;~~ ~~3. A conductive oxide sintered body according to paragraph 1 above, characterized in that the resistivity is or 300μΩcm or less.~~ ; ~~4. A~~ The conductive oxide sintered body according to each of paragraphs 1 to 3 above, characterized in containing contains 0.3mol% to 1.2mol% of Bi<sub>2</sub>O<sub>3</sub> ; and ~~5. A conductive oxide sintered body according to each of paragraphs 1 to 3 above, characterized in containing or 0.5mol% (and above) to 1.0mol% of Bi<sub>2</sub>O<sub>3</sub>.~~

Kindly replace the paragraph on page 3, lines 1-11, with the following amended paragraph:

The present invention further provides : ~~6. A~~ a sputtering target formed from a SrRuO<sub>3</sub> conductive oxide sintered body characterized in that the relative density is 93% or more; ~~7. A sputtering target formed from a SrRuO<sub>3</sub> conductive oxide sintered body according to paragraph 6 above, characterized in that the resistivity is 500μΩcm or less ;~~ ~~8. A sputtering target formed from a SrRuO<sub>3</sub> conductive oxide sintered body according to paragraph 6 above, characterized in that the resistivity is or 300μΩcm or less.~~ ; ~~9. A~~ The sputtering target formed from a conductive oxide sintered body according to each of paragraphs 6 to 8 above, characterized in containing contains 0.3mol% to 1.2mol% of Bi<sub>2</sub>O<sub>3</sub> ; and ~~10. A sputtering target formed from a conductive oxide sintered body according to each of paragraphs 6 to 8 above, characterized in containing or 0.5mol% (and above) to 1.0mol% of Bi<sub>2</sub>O<sub>3</sub>.~~

Kindly replace the paragraph on page 3, lines 12-27, with the following amended paragraph:

The present invention additionally provides ~~÷11. A a~~ manufacturing method of a  $\text{SrRuO}_3$  conductive oxide sintered body or a sputtering target formed from the sintered body, characterized in that  $0.3\text{mol}\%$  to  $1.2\text{mol}\%$  of  $\text{Bi}_2\text{O}_3$  is added as a sintering auxiliary upon manufacturing the  $\text{SrRuO}_3$  conductive oxide sintered body; ~~12. A manufacturing method of a  $\text{SrRuO}_3$  conductive oxide sintered body or a sputtering target formed from the sintered body, characterized in that or~~  $0.5\text{mol}\%$  (and above) to  $1.0\text{mol}\%$  of  $\text{Bi}_2\text{O}_3$  is added as a sintering auxiliary upon manufacturing the  $\text{SrRuO}_3$  conductive oxide sintered body; ~~÷13. A~~ The manufacturing method of a  $\text{SrRuO}_3$  conductive oxide sintered body or a sputtering target formed from the sintered body [,] is characterized in that sintering is performed at a sintering temperature of  $1400$  to  $1700^\circ\text{C}$  upon manufacturing the  $\text{SrRuO}_3$  conductive oxide sintered body; ~~÷and 14. A manufacturing method of a  $\text{SrRuO}_3$  conductive oxide sintered body or a sputtering target formed from the sintered body according to paragraph 11 or paragraph 12 above, characterized in that sintering is performed at a sintering temperature of  $1400$  to  $1700^\circ\text{C}$  upon manufacturing the  $\text{SrRuO}_3$  conductive oxide sintered body.~~

Kindly replace the paragraph on page 4, lines 19-23, with the following amended paragraph:

Upon manufacturing the  $\text{SrRuO}_3$  conductive oxide sintered body of the present invention,  $0.3\text{mol}\%$  to  $1.2\text{mol}\%$  of  $\text{Bi}_2\text{O}_3$  is added as an auxiliary agent. Preferably, sintering is performed upon adding  $0.5\text{mol}\%$  (and above) to  $1.0\text{mol}\%$  of  $\text{Bi}_2\text{O}_3$ . Thereby,  $0.3\text{mol}\%$  to  $1.2\text{mol}\%$  of  $\text{Bi}_2\text{O}_3$ , preferably  $0.5\text{mol}\%$  (and above) to  $1.0\text{mol}\%$  of  $\text{Bi}_2\text{O}_3$  is contained in the  $\text{SrRuO}_3$  conductive oxide sintered body and sputtering target.

Kindly replace the paragraph on page 4, lines 24-27, with the following amended paragraph:

In order to improve the sinterability and obtain a high density  $\text{SrRuO}_3$  conductive oxide sintered body, it is necessary to added  $0.3\text{mol}\%$  or more of  $\text{Bi}_2\text{O}_3$ , and preferably more than  $0.5\text{mol}\%$  of  $\text{Bi}_2\text{O}_3$  is added. If less than  $0.3\text{mol}\%$  of  $\text{Bi}_2\text{O}_3$  is added, it is not possible to achieve a density of 93% or more.

Kindly replace the paragraph on page 4, line 28, to page 5, line 4, with the following amended paragraph:

However, when the  $\text{Bi}_2\text{O}_3$  contained in the  $\text{SrRuO}_3$  conductive oxide sintered body and sputtering target increases, the  $\text{Bi}_2\text{O}_3$  contained in the sputtering film will increase, and the resistivity tends to increase. Moreover, when the amount of addition exceeds 1.2mol%, a second layer is formed in the sputtering film, this generates a Bi compound at the boundary face with the BSTO film or PZT film, and causes a problem of deteriorating the dielectric property. In consideration of the above, the upper limit of the additive amount has been set to 1.2mol%, and preferably to 1.0mol%.